

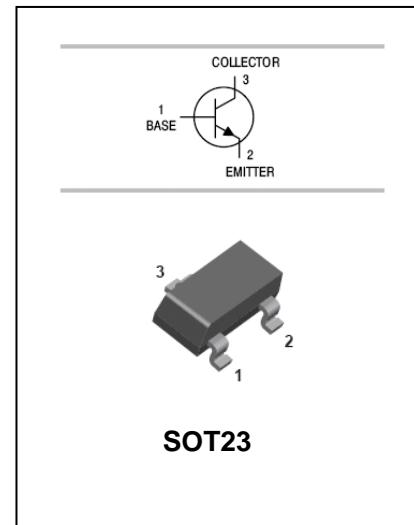
NPN SWITCHING TRANSISTOR

FEATURES

- Epitaxial planar die construction.
- Complementary PNP type available (MMBT3906).
- Collector Current Capability $I_{CM} = 200\text{mA}$.
- Collector-emitter Voltage $V_{CEO}=40\text{V}$.
- MSL 3



Lead-free



APPLICATIONS

- General switching and amplification

ORDERING INFORMATION

| Type No. | Marking | Package Code |
|-----------|---------|--------------|
| MMBT3904X | 1AM | SOT23 |

MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | Value | UNIT |
|-----------|-------------------------------|---------------------------------|-------------|------|
| V_{CBO} | collector-base voltage | open emitter | 60 | V |
| V_{CEO} | collector-emitter voltage | open base | 40 | V |
| V_{EBO} | emitter-base voltage | open collector | 6 | V |
| I_C | collector current (DC) | | 200 | mA |
| P_{tot} | total power dissipation | $T_{amb} \leq 25^\circ\text{C}$ | 200 | mW |
| T_{stg} | storage temperature | | -55 to +150 | °C |
| T_j | junction temperature | | 150 | °C |
| T_{amb} | operating ambient temperature | | -55 to +150 | °C |

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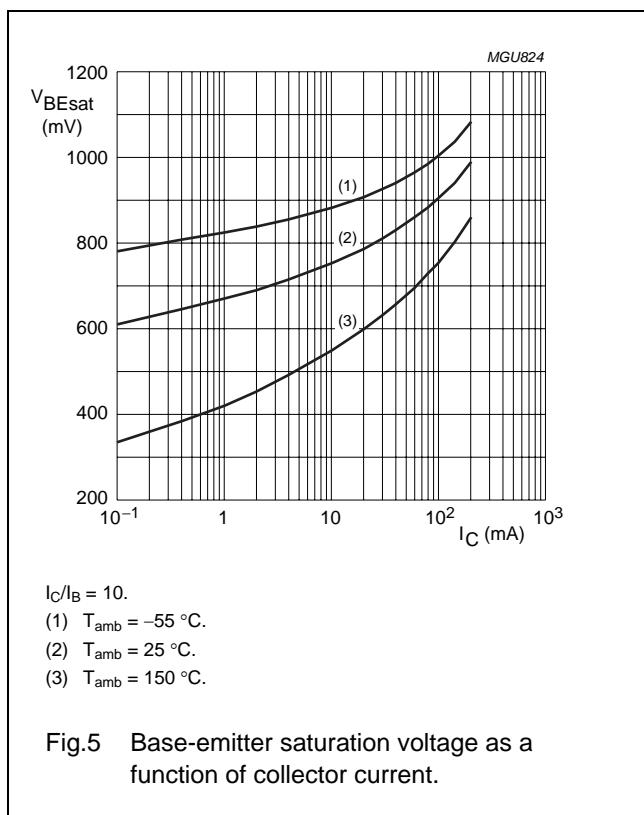
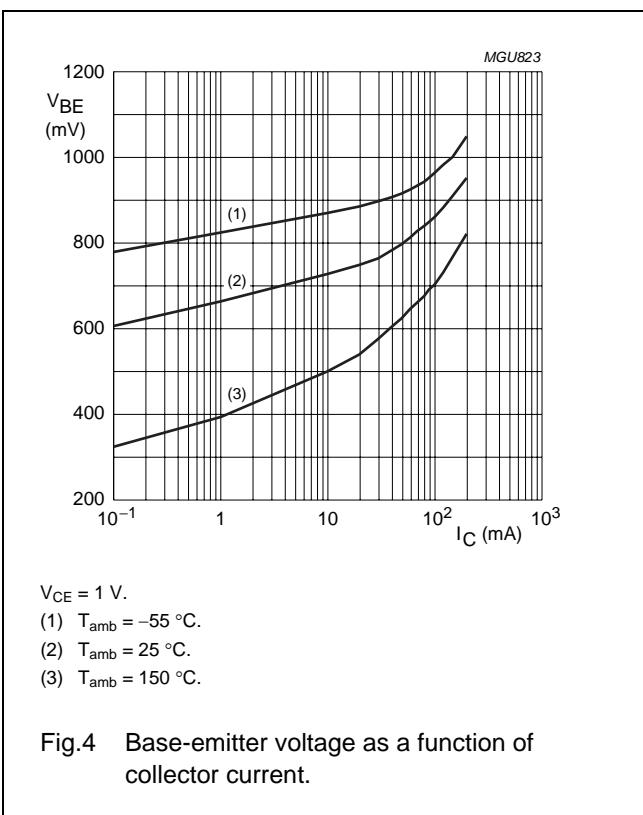
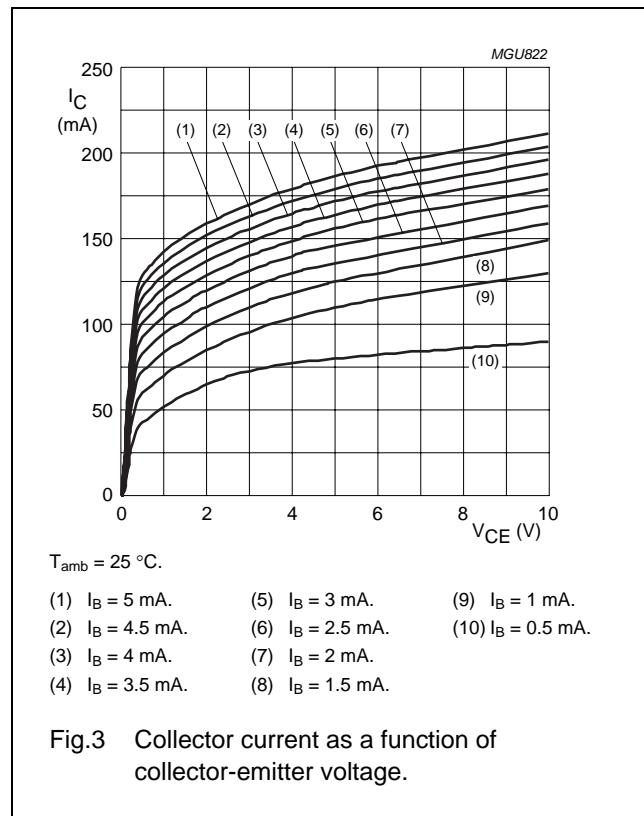
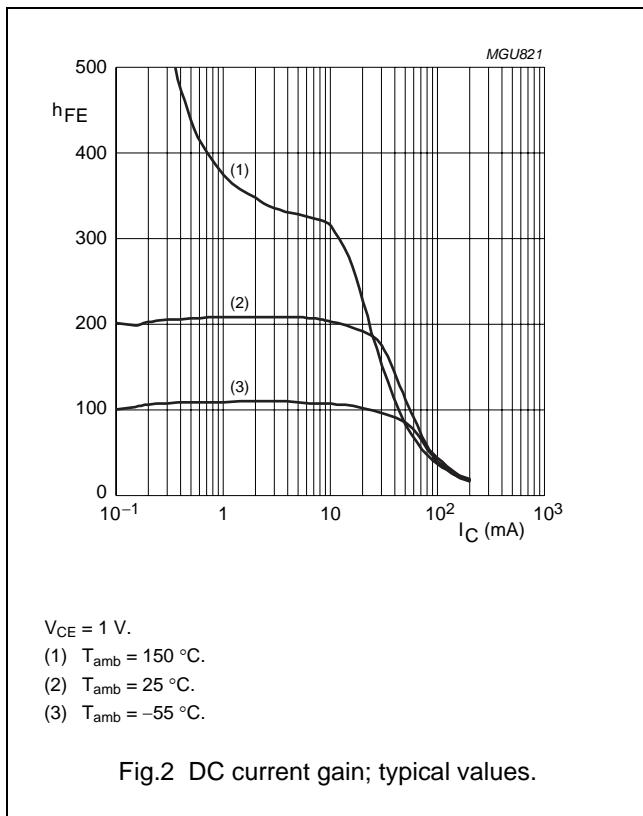
ELECTRICAL CHARACTERISTICS @ $T_a=25^\circ C$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|---|--------------------------------------|---|-----------------|---------------|------|
| I_{CBO} | collector cut-off current | $I_E = 0; V_{CB} = 60 \text{ V}$ | - | 0.1 | uA |
| I_{EBO} | emitter cut-off current | $I_C = 0; V_{EB} = 5 \text{ V}$ | - | 0.1 | uA |
| h_{FE} | DC current gain | $V_{CE} = 1 \text{ V};$ $I_C = 10\text{mA}$ $I_C = 50\text{mA}$ $I_C = 100\text{mA}$ | 100 60 30 | - 300 - | |
| $V_{CE(\text{sat})}$ | collector-emitter saturation voltage | $I_C = 10\text{mA}; I_B = 1\text{mA}$ | - | 200 | mV |
| | | $I_C = 50\text{mA}; I_B = 5\text{mA}$ | - | 300 | mV |
| $V_{BE(\text{sat})}$ | base-emitter saturation voltage | $I_C = 10\text{mA}; I_B = 1\text{mA}$ | 650 | 850 | mV |
| | | $I_C = 50\text{mA}; I_B = 5\text{mA}$ | - | 950 | mV |
| f_T | transition frequency | $I_C = 10\text{mA}; V_{CE} = 20\text{V};$ $f = 100\text{MHz}$ | 300 | - | MHz |
| Switching times (between 10% and 90% levels); | | | | | |
| t_d | delay time | $V_{CC}=3\text{Vdc}, V_{BE}=-0.5\text{Vdc}$ | - | 35 | ns |
| t_r | rise time | | - | 35 | ns |
| t_s | storage time | $V_{CC}=3\text{Vdc}, I_C=10\text{mAdc}$ | - | 200 | ns |
| t_f | fall time | | - | 50 | ns |

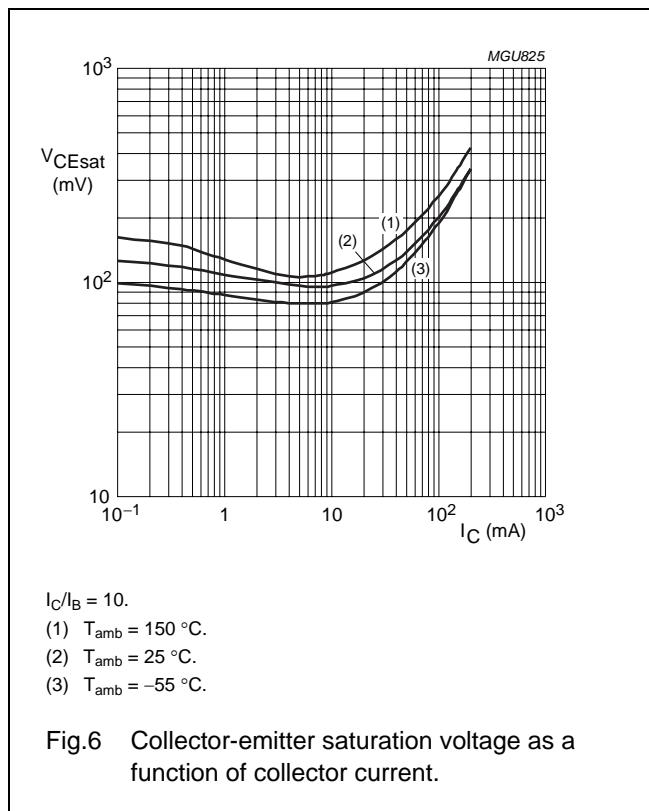
Note Pulse test: $t_p \leq 300 \text{ ms}$; $d \leq 0.02$.

NPN SWITCHING TRANSISTOR

TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified



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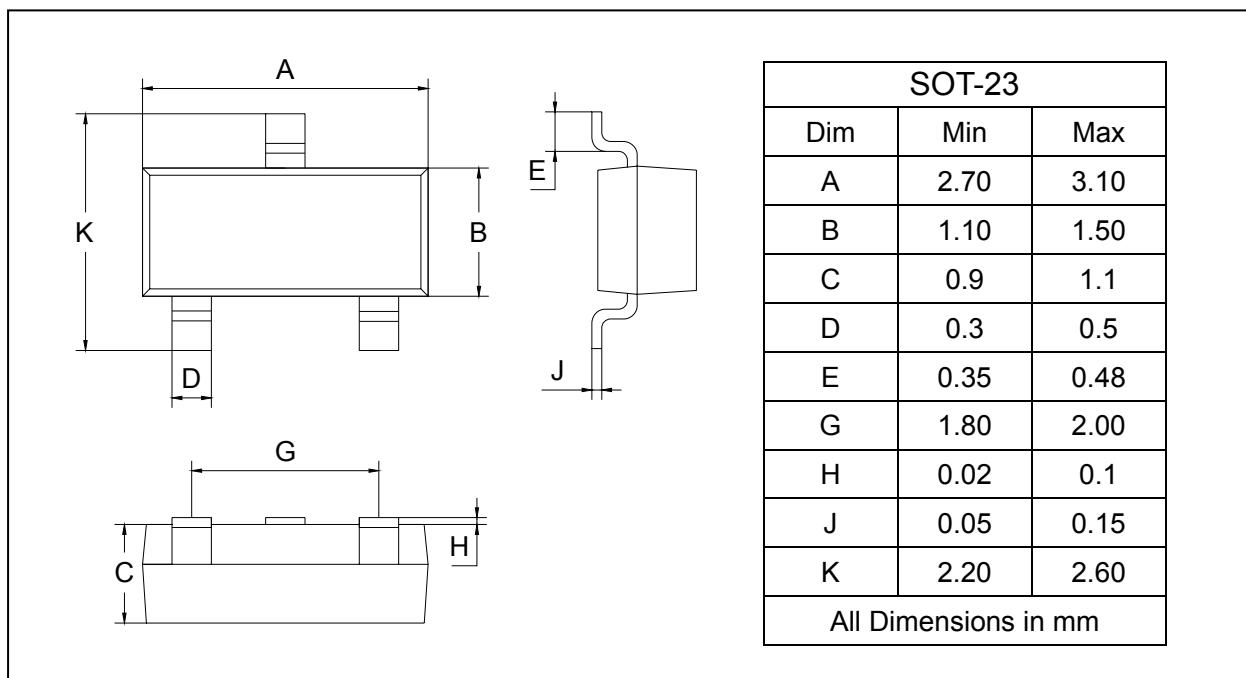


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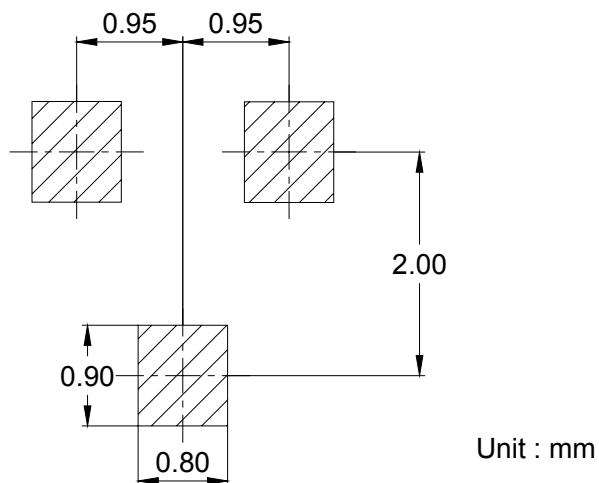
PACKAGE OUTLINE

Plastic surface mounted package

SOT23



SOLDERING FOOTPRINT



PACKAGE INFORMATION

| Device | Package | Shipping |
|----------|---------|----------------|
| MMBT3904 | SOT23 | 3000/Tape&Reel |